ELSEVIER

Thin Solid Films 364 (2000) 297–298

thin solid films

Author Index of Volume 364

Aboughe-Nze, P., 107
Abraham, P., 192
Aktsipetrov, O.A., 91
Allwood, D.A., 33
Andreev, A.D., 291
Anthony, C.J., 200
Antonov, V.N., 171
Arnaud d'Avitaya, F., 75
Aspnes, D.E., 22, 98

Batchelor, A.D., 98
Bauer, M., 228
Bayer, M., 220
Becker, M., 119
Beechinor, J.T., 58, 75, 244
Bell, K.A., 22
Benferhat, R., 213
Bentoumi, G., 107, 114
Bikbajevas, V., 181
Birdwell, A.G., 171
Bland, S.W., 58, 244
Bobek, T., 95
Boher, P., 53
Bonafos, C., 233
Bonan, J., 53
Borgström, M., 161
Borkovskaya, O.Y., 280
Bormann, D., 124
Bouanani, A., 124
Bozzo, S., 75
Bremser, M.D., 98
Brunson, K.M., 200
Bryja, L., 287
Bukkems, H.G., 165
Bustarret, E., 107, 114
Buyanova, I.A., 98

Callard, S., 264
Carline, R.T., 33
Certier, M., 124
Chen, W.M., 45
Cimalla, V., 28
Ciorga, M., 287
Claeys, C., 259
Cobet, C., 98, 111
Collins, R.W., 16, 129
Coonan, B.P., 75
Cordero, N., 58
Crean, G.M., 58, 75, 244
Cuadras, A., 233

Daudin, B., 107
Daudin, B., 114
Davis, R.F., 98
Dekorsy, T., 95
Demangeot, F., 156
Deneuville, A., 107, 114
Derbali, M.B., 192
Derrien, J., 75
Dittrich, Th., 196
Djurišić, A.B., 239
Dmitruk, N.L., 280
Dolgova, T.V., 91
Donchev, V., 224
Downer, M.C., 1, 80

Ebert, M., 22
Edwards, N.V., 98, 111
Eifler, G., 228
Ekerdt, J.G., 1
Esser, N., 98, 111

Fahsold, G., 177
Fantoni, A., 204
Farrell, I.L., 58
Fedyanin, A.A., 91
Ferlauto, A.S., 129
Fernandes, M., 204
Feuillet, G., 107, 114
Finkman, E., 53
Flock, K., 22
Fonseca, L., 233
Forchel, A., 220
Frandon, J., 156
Franz, M., 233
Fried, M., 64, 150
Füller, T., 119
Füssel, W., 196

Gagnaire, A., 264
Galeckas, A., 181
Garrido, B., 233
Gavrilenko, V.I., 1
Gensch, M., 12
Germanova, K., 224
Geurts, J., 119
Gioti, M., 213
Gleize, J., 156
Gorochov, O., 124
Goullet, A., 144
Grandjean, N., 156
Griffin, N., 75
Grigoryan, S.G., 284
Grimm, K., 254
Grivickas, V., 181
Gruska, B., 138, 165
Gyulai, J., 150

Hartmann, Th., 209
Heimbrodt, W., 209
Heime, K., 287
Henrion, W., 171
Heuken, M., 287
Holländer, B., 75
Hong, J., 144
Hopkinson, M., 6
Hovsepyan, R.K., 284

Ioffe, A.F., 249
Ivanov, I., 224

Jarasiunas, K., 186
Jepsen, O., 171
Joseph, J., 264
Jung, W., 274

Kafadaryan, E.A., 284
Kasper, E., 228
Kechagias, V.G., 213
Kelly, P.V., 58, 244
Key, P.H., 200
Khelifa, B., 124
Kildemo, M., 244
Klar, P.J., 209
Kleverman, M., 161
Kobayashi, K., 259
Koeth, J., 220
Koh, J., 129
Kokhanovskii, S.I., 249
Korn, M., 119
Koval, R.J., 129
Kristensen, T.B., 86
Kuball, M., 156
Kubisa, M., 220
Kudou, T., 259
Kuroda, K., 186
Kurz, H., 95

Lampalzer, M., 209
Landin, L., 161
Lazreg, A., 124
Lazzari, J.-L., 75
Lee, Y., 129
Lee, Y.-S., 80
Lehnert, W., 150
Li, E.H., 239
Lim, D., 1
Linnros, J., 181
Logothetidis, S., 213
Lohner, T., 150
Lorberth, J., 209
Lovergine, N., 186
Lunk, A., 40

Maçarico, A., 204
Madsen, L.D., 98
Magg, N., 177
Mamontova, I.B., 280
Mantl, S., 75
Manukyan, A.L., 284
Marowsky, G., 91
Martinez, E., 107
Martins, J., 204
Masenelli, B., 264
Mason, N.J., 33
Massies J., 156
Mayeva, O.I., 280
Meddeb, J., 192
Megges, K., 209
Messier, R., 16
Meyer, F., 53
Meyne, C., 12
Misiewicz, J., 220, 287
Mizeikis, V., 186
Monemar, B., 98
Monteil, Y., 107
Morante, J.R., 233
Moriarty, G.R., 244

PII: S0040-6090(00)00908-1

Moumanis, Kh., 249
Murtagh, M., 58, 75, 244

Nakabayashi, M., 259
Nanver, L.K., 254

O'Connor, G.M., 58
Oehme, M., 228
Oei, Y.S., 165
Ohyama, H., 259
O'Reilly, E.P., 291
Ozanyan, K.B., 6

Pagès, O., 124
Parbrook, P.J., 6
Parkinson, P., 1
Paul, D.J., 75
Pedersen, K., 86
Pedersen, T.G., 86
Peters, S., 12
Petrenko, A.B., 196
Petrik, P., 150
Pezoldt, J., 28
Pickering, C., 33
Piotrowski, T., 274
Pistol, M.-E., 161
Pohl, U.W., 12
Polit, J., 269
Pressel, K., 233
Priebe, A., 177
Pucci, A., 177

Rakovich, Y., 287
Rappich, J., 196
Rebien, M., 171
Rédei, L., 64
Redmond, G., 75
Renucci, M.A., 156
Richter, U., 165
Richter, W., 12, 111
Rovira, P.I., 129
Ryczko, K., 220
Ryssel, H., 150

Samuelson, L., 161
Sands, D., 200
Sasin, M.E., 249
Sauter, M., 228
Schaefer, J.A., 28
Scheible, P., 40
Schlaf, M., 200
Schneider, C., 150
Schuhmacher, D., 91
Schwarz, R., 204
Sciesińska, E., 269
Sciesiński, J., 269
Seifert, W., 161
Seisyan, R.P., 249
Sęk, G., 220
Sheregii, E.M., 269
Shi, J.L., 254
Shtinkov, N., 224
Simoen, E., 259
Stauden, Th., 28
Stein, J., 95
Stolz, W., 209
Sunaga, H., 259
Svob, L., 124

Takami, Y., 259
Tanner, B.K., 33
Teer, D., 213
Tellefsen, J.A., 181
Thiandoume, C., 124
Timoshenko, V.Y., 196
Turban, G., 144

Uren, M.J., 200

Vardanyan, E.S., 284
Vardanyan, R.S., 284
Vieira, M., 204
Visser, C.C.G., 254
Vlaev, S., 224

Wagner, V., 119
Walker, P.J., 33
Walton, C.D., 200
Wang, T., 220
Warren, P., 53
Weber, M., 119
Wethkamp, T., 98, 111
Whitehouse, C.R., 6
Wilmers, K., 98, 111
Wöhner, T., 28
Wronski, C.R., 129
Wu, R.Q., 1

Yablonskii, G.P., 287
Yastrubchak, O.B., 280
Yoneoka, M., 259
Yoo, S.D., 22, 98

Zaoui, A., 124
Zapien, J.A., 16
Zettler, J.-T., 12
Zhang, X.H., 161

ELSEVIER

Thin Solid Films 364 (2000) 299–305

thin solid films

Subject Index of Volume 364

a-C:H film
Optical characterization of hydrogenated amorphous carbon (*a*-C:H) thin films deposited from methane plasma, 144
Absorption
Spatially and time-resolved infrared absorption for optical and electrical characterization of indirect band gap semiconductors, 181
Absorption spectra
Light and heavy hole excitons in absorption and magnetoabsorption spectra of InGaAs/GaAs MQWs, 249
Acid-polished
Characterization of oxide layers on GaAs substrates, 33
AlAs/GaAs superlattices
Photoluminescence study of AlAs/GaAs superlattices containing enlarged wells, 224
AlGaN
Resonant Raman scattering in (Al,Ga)N/GaN quantum well structures, 156
Alq_3
Fabrication and characterization of organic semiconductor-based microcavities, 264
Amorphous silicon
Real time analysis of amorphous and microcrystalline silicon film growth by multichannel ellipsometry, 129
Amorphous to crystalline transition/transformation
Time resolved reflectivity measurements of silicon solid phase epitaxial regrowth, 228

Band structure
Optical interband spectra and band structure of Ru_2Si_3 and Ru_2Ge_3, 171
Boron nitride
Real-time spectroscopic ellipsometry from 1.5 to 6.5 Ev, 16
Buried heterostructure laser diodes
Impact of neutron irradiation on optical performance of InGaAsP laser diodes, 259

Carbonization process
Real time spectroscopic ellipsometry monitoring of the SiC growth during the interaction process of elemental carbon with Si surfaces, 28
Carrier spectrum
Theoretical analysis of strain distribution, carrier spectrum and gain in GaN-based hexagonal QDs, 291
CdTe
Non-destructive optical characterization of the surface region in bulk semiconductors and heterostructures, 186
Characterization
Sensitivity of SHG-measurements on oxide deposition process parameters, 95
Classical size effect
An IR-transmission spectroscopical study of the influence of substrate surface defects on the morphology and the electronic structure of ultrathin Fe grown on MgO(001), 177
Conductivity
Far-infrared conductivity of the $PbZr_{0.52}Ti_{0.48}O_3$ and Cu-doped $PbTiO_3$ ferroelectric thin films, 284
Coupled quantum wells
Photoreflectance spectroscopy of coupled $In_xGa_{1-x}As/GaAs$ quantum wells, 220
Cubic boron nitride
In situ characterization of boron nitride layer growth by polarized FTIR reflection spectroscopy, 40
Cubic Gallium nitride
Si doping of cubic heteroepitaxial GaN layers studied by Raman scattering, 107
Cubic Silicon carbibe
Si doping of cubic heteroepitaxial GaN layers studied by Raman scattering, 107

Deep levels
Impact of neutron irradiation on optical performance of InGaAsP laser diodes, 259
Defects
Applications of optically detected magnetic resonance in semiconductor layered structures, 45
Density functional theory
Optical second harmonic spectra of silicon-adatom surfaces: theory and experiment, 1
Depth profiling
Non-destructive optical depth profiling and real-time evaluation of spectroscopic data, 64
Dielectric functions
Carbon dependence of the dielectric response function in epitaxial SiGeC layers grown on Si, 53
Application of the reflection–absorption spectroscopy to the semiconductor thin films, 269
Diffraction grating
Ultraviolet responsivity control in Schottky barrier heterostructures with textured interface, 280
Diluted magnetic semiconductor
Optical characterisation of MOVPE-grown $Ga_{1-x}Mn_xAs$ semimagnetic semiconductor layers, 209
Dispersion description
Analysis of III–V layer stacks on INP substrates using spectroscopic ellipsometry in the NIR spectral range, 165

PII: S0040-6090(00)00909-3

Dual ECR-r.f. plasma
Optical characterization of hydrogenated amorphous carbon (*a*-C:H) thin films deposited from methane plasma, 144
Dynamic conductivity
An IR-transmission spectroscopical study of the influence of substrate surface defects on the morphology and the electronic structure of ultrathin Fe grown on MgO(001), 177

Efficiency
VIS/NIR detector based on μc-Si:H p–i–n structures, 204
Electron spin resonance
Applications of optically detected magnetic resonance in semiconductor layered structures, 45
Electronic properties
Spatially and time-resolved infrared absorption for optical and electrical characterization of indirect band gap semiconductors, 181
Electroreflectance
Raman and electroreflectance analysis of internal electric fields in ZnSe, 119
Ellipsometry
Optical interband spectra and band structure of Ru_2Si_3 and Ru_2Ge_3, 171
'Real-time' multiwavelength ellipsometry diagnostics for monitoring dry etching of Si and TiN_x deposition, 213
Optical characterization of thermally oxidized $Si_{1-x-y}Ge_xC_y$ layers, 233
Optical and structural properties of InGaP heterostructures, 244
Enlarged wells
Photoluminescence study of AlAs/GaAs superlattices containing enlarged wells, 224
Epilayers
Effect of above band-gap illumination on structure of free exciton reflection spectra of ZnSe, 287
Epitaxial layers
Time resolved photoluminescence of homo- and hetero-epitaxial layers of InP grown on GaAs substrates, 192
Excitons
Optical characterization of wide bandgap semiconductors, 98
Extended source
Characterization of silicon wafer bonding by observation in transmitted infrared radiation from an extended source, 274

Far-infrared Spectra
Far-infrared conductivity of the $PbZr_{0.52}Ti_{0.48}O_3$ and Cu-doped $PbTiO_3$ ferroelectric thin films, 284
Film characterization
Optical characterization of hydrogenated amorphous carbon (*a*-C:H) thin films deposited from methane plasma, 144
Film thickness measurement
Ellipsometric analysis of polysilicon layers, 138
Fine free exciton structure
Effect of above band-gap illumination on structure of free exciton reflection spectra of ZnSe, 287
Forbidden transition
Photoreflectance spectroscopy of coupled $In_xGa_{1-x}As$/GaAs quantum wells, 220
Fourth harmonic generation
Reflected optical fourth harmonic generation at crystalline surfaces, 80
Four-wave mixing
Non-destructive optical characterization of the surface region in bulk semiconductors and heterostructures, 186
Franz–Keldysh effect
Raman and electroreflectance analysis of internal electric fields in ZnSe, 119

GaAs
Raman analysis of LO phonon–plasmon coupled modes at ZnS:N/(n^+,p^+)–GaAs interfaces, 124
Non-destructive optical characterization of the surface region in bulk semiconductors and heterostructures, 186
Optical characterisation of MOVPE-grown $Ga_{1-x}Mn_xAs$ semimagnetic semiconductor layers, 209
Ultraviolet responsivity control in Schottky barrier heterostructures with textured interface, 280
GaAs substrates
Characterization of oxide layers on GaAs substrates, 33
Time resolved photoluminescence of homo- and hetero-epitaxial layers of InP grown on GaAs substrates, 192
GaAs/InGaAs
Non-destructive optical characterization of the surface region in bulk semiconductors and heterostructures, 186
Gain
Theoretical analysis of strain distribution, carrier spectrum and gain in GaN-based hexagonal QDs, 291
Gallium phosphide
In situ monitoring of MOVPE growth by combined spectroscopic ellipsometry and reflectance-difference spectroscopy, 22
Gallium nitride
Optical characterization of wide bandgap semiconductors, 98
Resonant Raman scattering in (Al,Ga)N/GaN quantum well structures, 156
GaN films
Strain in cubic GaN films versus residual hexagonal GaN content, 114
Growth
Static and growing InP and InAs surfaces: reflection-anisotropy spectroscopy under the conditions of solid-source MBE, 6
Growth control
In situ monitoring of MOVPE growth by combined spectroscopic ellipsometry and reflectance-difference spectroscopy, 22

Heterojunction
Ultraviolet responsivity control in Schottky barrier heterostructures with textured interface, 280
Heterostructure field-effect transistor
Investigation of Si/SiGe heterostructure material using non-destructive optical techniques, 75
Heterostructures
Raman and electroreflectance analysis of internal electric fields in ZnSe, 119
Hexagonal GaN content
Strain in cubic GaN films versus residual hexagonal GaN content, 114
Hole excitons

Light and heavy hole excitons in absorption and magnetoabsorption spectra of InGaAs/GaAs MQWs, 249
In situ
Static and growing InP and InAs surfaces: reflection-anisotropy spectroscopy under the conditions of solid-source MBE, 6
In situ analysis
Real time spectroscopic ellipsometry monitoring of the SiC growth during the interaction process of elemental carbon with Si surfaces, 28
In situ ellipsometry
In situ spectroscopic ellipsometry for the characterization of polysilicon formation inside a vertical furnace, 150
Indium arsnide
Optical investigation of InAs/InP quantum dots at different temperatures and under electric field, 161
Indium phosphide
Ultraviolet responsivity control in Schottky barrier heterostructures with textured interface, 280
Infrared reflection absorption spectroscopy
In situ characterization of boron nitride layer growth by polarized FTIR reflection spectroscopy, 40
Infrared spectroscopic ellipsometry
In situ characterization of boron nitride layer growth by polarized FTIR reflection spectroscopy, 40
Infrared spectroscopy
An IR-transmission spectroscopical study of the influence of substrate surface defects on the morphology and the electronic structure of ultrathin Fe grown on MgO(001), 177
Infra-red reflectivity of ion-implanted and pulsed excimer laser irradiated 4H-SiC, 200
Optical characterization of thermally oxidized $Si_{1-x-y}Ge_xC_y$ layers, 233
InGaAs/GaAs
Light and heavy hole excitons in absorption and magnetoabsorption spectra of InGaAs/GaAs MQWs, 249
InGaAsP
Impact of neutron irradiation on optical performance of InGaAsP laser diodes, 259
InGaP/GaAs
Optical and structural properties of InGaP heterostructures, 244
InGaP/GaAs HBT
InGaP/GaAs heterojunction bipolar transistor optical and electronic band structure characterization, 58
Indium phosphide
Optical investigation of InAs/InP quantum dots at different temperatures and under electric field, 161
InP-based layer stacks
Analysis of III–V layer stacks on INP substrates using spectroscopic ellipsometry in the NIR spectral range, 165
Interface
Sensitivity of SHG-measurements on oxide deposition process parameters, 95
Intermixing
InGaP/GaAs heterojunction bipolar transistor optical and electronic band structure characterization, 58
Photoluminescence study of AlAs/GaAs superlattices containing enlarged wells, 224
Optical and structural properties of InGaP heterostructures, 244
Internal collection
VIS/NIR detector based on μc-Si:H p–i–n structures, 204
Ion etching
'Real-time' multiwavelength ellipsometry diagnostics for monitoring dry etching of Si and TiN_x deposition, 213
Ion implantation
Non-destructive optical depth profiling and real-time evaluation of spectroscopic data, 64
Iron
An IR-transmission spectroscopical study of the influence of substrate surface defects on the morphology and the electronic structure of ultrathin Fe grown on MgO(001), 177

Laser irradiation
Infra-red reflectivity of ion-implanted and pulsed excimer laser irradiated 4H-SiC, 200
LO phonon–plasmon coupling
Raman analysis of LO phonon–plasmon coupled modes at ZnS:N/(n^+,p^+)–GaAs interfaces, 124
Luminescence
Applications of optically detected magnetic resonance in semiconductor layered structures, 45
Photoluminescence characterization of non-radiative defect density on silicon surfaces and interfaces at room temperature, 196

Magneto-optics
Optical characterisation of MOVPE-grown $Ga_{1-x}Mn_xAs$ semimagnetic semiconductor layers, 209
Metallic quantum wells
Optical second-harmonic generation as a probe of quantum well states in ultrathin Au and Ag films deposited on Si(111), 86
Metalorganic chemical vapor deposition
Time resolved photoluminescence of homo- and hetero-epitaxial layers of InP grown on GaAs substrates, 192
Metalorganic vapor phase epitaxy
In situ monitoring of ZnS/GaP and ZnSe/GaAs metalorganic vapor phase epitaxy using reflectance anisotropy spectroscopy and spectroscopic ellipsometry, 12
In situ monitoring of MOVPE growth by combined spectroscopic ellipsometry and reflectance-difference spectroscopy, 22
Optical characterisation of MOVPE-grown $Ga_{1-x}Mn_xAs$ semimagnetic semiconductor layers, 209
Magnesium oxide
An IR-transmission spectroscopical study of the influence of substrate surface defects on the morphology and the electronic structure of ultrathin Fe grown on MgO(001), 177
Microcavity
Fabrication and characterization of organic semiconductor-based microcavities, 264
Microcrystalline hydrogenated silicon
VIS/NIR detector based on μc-Si:H p–i–n structures, 204
Microcrystalline silicon
Real time analysis of amorphous and microcrystalline silicon film growth by multichannel ellipsometry, 129
Micro-Raman
Strain in cubic GaN films versus residual hexagonal GaN content, 114
Microrelief

Ultraviolet responsivity control in Schottky barrier heterostructures with textured interface, 280
Microstructural evolution
Real time analysis of amorphous and microcrystalline silicon film growth by multichannel ellipsometry, 129
Misfit dislocations
Defect related photoluminescence of SiGe/Si heterostructures grown by APCVD, 254
Mobility
Si doping of cubic heteroepitaxial GaN layers studied by Raman scattering, 107
Molecular beam epitaxy
Time resolved reflectivity measurements of silicon solid phase epitaxial regrowth, 228
Monitoring
Static and growing InP and InAs surfaces: reflection-anisotropy spectroscopy under the conditions of solid-source MBE, 6
Multiple quantum well
Light and heavy hole excitons in absorption and magnetoabsorption spectra of InGaAs/GaAs MQWs, 249

Neural networks
Non-destructive optical depth profiling and real-time evaluation of spectroscopic data, 64
Nitrogen
Raman analysis of LO phonon–plasmon coupled modes at ZnS:N/(n^+,p^+)–GaAs interfaces, 124
Non-destructive characterization
Non-destructive optical characterization of the surface region in bulk semiconductors and heterostructures, 186
Non-ionizing energy loss
Impact of neutron irradiation on optical performance of InGaAsP laser diodes, 259
Non-linear optics
Sensitivity of SHG-measurements on oxide deposition process parameters, 95

Optical constants
Optical interband spectra and band structure of Ru_2Si_3 and Ru_2Ge_3, 171
Time resolved reflectivity measurements of silicon solid phase epitaxial regrowth, 228
Optical dielectric function of semiconductors, 239
Optical properties
Carbon dependence of the dielectric response function in epitaxial SiGeC layers grown on Si, 53
Optical characterization of hydrogenated amorphous carbon (*a*-C:H) thin films deposited from methane plasma, 144
Optical spectroscopy
Spatially and time-resolved infrared absorption for optical and electrical characterization of indirect band gap semiconductors, 181
Optically detected magnetic resonance
Applications of optically detected magnetic resonance in semiconductor layered structures, 45
Ordering
InGaP/GaAs heterojunction bipolar transistor optical and electronic band structure characterization, 58
Optical and structural properties of InGaP heterostructures, 244
Oxide layers
Characterization of oxide layers on GaAs substrates, 33

$PbTiO_3$
Far-infrared conductivity of the $PbZr_{0.52}Ti_{0.48}O_3$ and Cu-doped $PbTiO_3$ ferroelectric thin films, 284
Phase measurements
Optical second-harmonic phase spectroscopy of the Si(111)–SiO_2 interface, 91
Phonons
Resonant Raman scattering in (Al,Ga)N/GaN quantum well structures, 156
Application of the reflection–absorption spectroscopy to the semiconductor thin films, 269
Photocurrent
VIS/NIR detector based on μc-Si:H p–i–n structures, 204
Photoluminescence
InGaP/GaAs heterojunction bipolar transistor optical and electronic band structure characterization, 58
Optical investigation of InAs/InP quantum dots at different temperatures and under electric field, 161
Photoluminescence spectroscopy
Photoluminescence study of AlAs/GaAs superlattices containing enlarged wells, 224
Defect related photoluminescence of SiGe/Si heterostructures grown by APCVD, 254
Photoreflectance
InGaP/GaAs heterojunction bipolar transistor optical and electronic band structure characterization, 58
Photoreflectance spectroscopy
Photoreflectance spectroscopy of coupled $In_xGa_{1-x}As$/GaAs quantum wells, 220
Plasma resonance
Ultraviolet responsivity control in Schottky barrier heterostructures with textured interface, 280
Polarized FTIR reflection spectroscopy
In situ characterization of boron nitride layer growth by polarized FTIR reflection spectroscopy, 40
Polycrystalline silicon
Ellipsometric analysis of polysilicon layers, 138
In situ spectroscopic ellipsometry for the characterization of polysilicon formation inside a vertical furnace, 150
Porous silicon
Non-destructive optical depth profiling and real-time evaluation of spectroscopic data, 64

Quantum dot
Optical investigation of InAs/InP quantum dots at different temperatures and under electric field, 161
Quantum dot lasers
Theoretical analysis of strain distribution, carrier spectrum and gain in GaN-based hexagonal QDs, 291
Quantum wells
Resonant Raman scattering in (Al,Ga)N/GaN quantum well structures, 156

Radiation damage
Impact of neutron irradiation on optical performance of InGaAsP laser diodes, 259

Radiation source dependence
Impact of neutron irradiation on optical performance of InGaAsP laser diodes, 259
Raman
Investigation of Si/SiGe heterostructure material using non-destructive optical techniques, 75
Si doping of cubic heteroepitaxial GaN layers studied by Raman scattering, 107
Optical and structural properties of InGaP heterostructures, 244
Resonant Raman scattering in (Al,Ga)N/GaN quantum well structures, 156
Raman analysis of LO phonon–plasmon coupled modes at ZnS:N/(n^+,p^+)–GaAs interfaces, 124

Real-time
'Real-time' multiwavelength ellipsometry diagnostics for monitoring dry etching of Si and TiN_x deposition, 213
Real-time analysis
Real-time spectroscopic ellipsometry from 1.5 to 6.5 Ev, 16
Real-time monitoring
In situ monitoring of MOVPE growth by combined spectroscopic ellipsometry and reflectance-difference spectroscopy, 22
Real time spectroscopic ellipsometry
Real time spectroscopic ellipsometry monitoring of the SiC growth during the interaction process of elemental carbon with Si surfaces, 28
Real time analysis of amorphous and microcrystalline silicon film growth by multichannel ellipsometry, 129
Reciprocal space analysis
Optical characterization of wide bandgap semiconductors, 98
Recombination
Applications of optically detected magnetic resonance in semiconductor layered structures, 45
Recovery
Impact of neutron irradiation on optical performance of InGaAsP laser diodes, 259
Recrystallization of amorphous silicon
Time resolved reflectivity measurements of silicon solid phase epitaxial regrowth, 228
Reflectance
Optical characterization of wide bandgap semiconductors, 98
Reflectance anistropy spectroscopy
In situ monitoring of ZnS/GaP and ZnSe/GaAs metalorganic vapor phase epitaxy using reflectance anisotropy spectroscopy and spectroscopic ellipsometry, 12
Reflectance-difference spectroscopy
In situ monitoring of MOVPE growth by combined spectroscopic ellipsometry and reflectance-difference spectroscopy, 22
Reflection spectroscopy
Infra-red reflectivity of ion-implanted and pulsed excimer laser irradiated 4H-SiC, 200
Reflection–absorption spectroscopy
Application of the reflection–absorption spectroscopy to the semiconductor thin films, 269
Reflection-anisotropy
Static and growing InP and InAs surfaces: reflection-anisotropy spectroscopy under the conditions of solid-source MBE, 6
Reflection supported pyrometric interferometry
Time resolved reflectivity measurements of silicon solid phase epitaxial regrowth, 228
3D Relaxation
Defect related photoluminescence of SiGe/Si heterostructures grown by APCVD, 254
Resonance
Resonant Raman scattering in (Al,Ga)N/GaN quantum well structures, 156
Resonant Raman spectroscopy
Raman and electroreflectance analysis of internal electric fields in ZnSe, 119
Ru_2Ge_3
Optical interband spectra and band structure of Ru_2Si_3 and Ru_2Ge_3, 171
Rutherford back-scattering spectroscopy
Investigation of Si/SiGe heterostructure material using non-destructive optical techniques, 75

Second harmonic generation
Optical second harmonic spectra of silicon-adatom surfaces: theory and experiment, 1
Reflected optical fourth harmonic generation at crystalline surfaces, 80
Optical second-harmonic generation as a probe of quantum well states in ultrathin Au and Ag films deposited on Si(111), 86
Optical second-harmonic phase spectroscopy of the Si(111)–SiO_2 interface, 91
Sensitivity of SHG-measurements on oxide deposition process parameters, 95
Semiconductors
Optical second harmonic spectra of silicon-adatom surfaces: theory and experiment, 1
Static and growing InP and InAs surfaces: reflection-anisotropy spectroscopy under the conditions of solid-source MBE, 6
Applications of optically detected magnetic resonance in semiconductor layered structures, 45
Optical dielectric function of semiconductors, 239
Silicides
Optical interband spectra and band structure of Ru_2Si_3 and Ru_2Ge_3, 171
Silicon
In situ monitoring of MOVPE growth by combined spectroscopic ellipsometry and reflectance-difference spectroscopy, 22
Spatially and time-resolved infrared absorption for optical and electrical characterization of indirect band gap semiconductors, 181
Photoluminescence characterization of non-radiative defect density on silicon surfaces and interfaces at room temperature, 196
Infra-red reflectivity of ion-implanted and pulsed excimer laser irradiated 4H-SiC, 200
Silicon(111)
Optical second-harmonic phase spectroscopy of the Si(111)–SiO_2 interface, 91
Silicon carbide
Spatially and time-resolved infrared absorption for optical and electrical characterization of indirect band gap semiconductors, 181

Silicon carbide growth
Real time spectroscopic ellipsometry monitoring of the SiC growth during the interaction process of elemental carbon with Si surfaces, 28
Silicon doping
Si doping of cubic heteroepitaxial GaN layers studied by Raman scattering, 107
Silicon dioxide
Sensitivity of SHG-measurements on oxide deposition process parameters, 95
Silicon-germanium
Defect related photoluminescence of SiGe/Si heterostructures grown by APCVD, 254
Silicon-germanium-carbon
Carbon dependence of the dielectric response function in epitaxial SiGeC layers grown on Si, 53
Silicon-germanium-carbon compound semiconductors
Optical characterization of thermally oxidized $Si_{1-x-y}Ge_xC_y$ layers, 233
Si/SiGe heterostructure
Investigation of Si/SiGe heterostructure material using non-destructive optical techniques, 75
Silicon oxide
Optical characterization of thermally oxidized $Si_{1-x-y}Ge_xC_y$ layers, 233
Silicon wafer bonding
Characterization of silicon wafer bonding by observation in transmitted infrared radiation from an extended source, 274

Smooth interfaces
Photoluminescence study of AlAs/GaAs superlattices containing enlarged wells, 224
Sol–gel
Far-infrared conductivity of the $PbZr_{0.52}Ti_{0.48}O_3$ and Cu-doped $PbTiO_3$ ferroelectric thin films, 284
Solar cells
Real time analysis of amorphous and microcrystalline silicon film growth by multichannel ellipsometry, 129
Solid phase epitaxy
Time resolved reflectivity measurements of silicon solid phase epitaxial regrowth, 228
Spectral responsivity
In situ monitoring of ZnS/GaP and ZnSe/GaAs metalorganic vapor phase epitaxy using reflectance anisotropy spectroscopy and spectroscopic ellipsometry, 12
Real-time spectroscopic ellipsometry from 1.5 to 6.5 Ev, 16
In situ monitoring of MOVPE growth by combined spectroscopic ellipsometry and reflectance-difference spectroscopy, 22
Non-destructive optical depth profiling and real-time evaluation of spectroscopic data, 64
Optical characterization of wide bandgap semiconductors, 98
Ellipsometric analysis of polysilicon layers, 138
In situ spectroscopic ellipsometry for the characterization of polysilicon formation inside a vertical furnace, 150
Analysis of III–V layer stacks on INP substrates using spectroscopic ellipsometry in the NIR spectral range, 165
VIS/NIR detector based on μc-Si:H p–i–n structures, 204
Fabrication and characterization of organic semiconductor-based microcavities, 264
Spectroscopy
Static and growing InP and InAs surfaces: reflection-anisotropy spectroscopy under the conditions of solid-source MBE, 6
Optical second-harmonic phase spectroscopy of the Si(111)–SiO_2 interface, 91
Strain
Optical characterization of wide bandgap semiconductors, 98
Optical and structural properties of InGaP heterostructures, 244
Strain distribution
Theoretical analysis of strain distribution, carrier spectrum and gain in GaN-based hexagonal QDs, 291
Surface defects
Photoluminescence characterization of non-radiative defect density on silicon surfaces and interfaces at room temperature, 196
Surface polariton
Ultraviolet responsivity control in Schottky barrier heterostructures with textured interface, 280
Surface reconstruction
Optical second harmonic spectra of silicon-adatom surfaces: theory and experiment, 1
Surfaces semiconductors
Reflected optical fourth harmonic generation at crystalline surfaces, 80

Temperature-dependance
Optical investigation of InAs/InP quantum dots at different temperatures and under electric field, 161
Textured interface
Ultraviolet responsivity control in Schottky barrier heterostructures with textured interface, 280
Thin films
An IR-transmission spectroscopical study of the influence of substrate surface defects on the morphology and the electronic structure of ultrathin Fe grown on MgO(001), 177
Thin film deposition
Real-time spectroscopic ellipsometry from 1.5 to 6.5 Ev, 16
Real time analysis of amorphous and microcrystalline silicon film growth by multichannel ellipsometry, 129
Tight binding
Optical second harmonic spectra of silicon-adatom surfaces: theory and experiment, 1
Time resolved reflectivity measurement
Time resolved reflectivity measurements of silicon solid phase epitaxial regrowth, 228
Time-resolved photoluminescence spectroscopy
Time resolved photoluminescence of homo- and hetero-epitaxial layers of InP grown on GaAs substrates, 192
Titanium nitride
'Real-time' multiwavelength ellipsometry diagnostics for monitoring dry etching of Si and TiN_x deposition, 213
Transient gratings
Non-destructive optical characterization of the surface region in bulk semiconductors and heterostructures, 186
Transmitted infrared radiation
Characterization of silicon wafer bonding by observation in transmitted infrared radiation from an extended source, 274
Tri-hydroxyquinoline-aluminum
Fabrication and characterization of organic semiconductor-based microcavities, 264

Type I and II quantum well
Photoreflectance spectroscopy of coupled $In_xGa_{1-x}As/GaAs$ quantum wells, 220

Ultraviolet
Real-time spectroscopic ellipsometry from 1.5 to 6.5 eV, 16
Ultraviolet photodetector
Ultraviolet responsivity control in Schottky barrier heterostructures with textured interface, 280

Valence bands
Optical characterization of wide bandgap semiconductors, 98
Variable angle spectroscopic ellipsometry
Investigation of Si/SiGe heterostructure material using non-destructive optical techniques, 75
VIS/NIR detectors
VIS/NIR detector based on μc-Si:H p–i–n structures, 204

Wafer mapping
Non-destructive optical depth profiling and real-time evaluation of spectroscopic data, 64

ZnS
Raman analysis of LO phonon–plasmon coupled modes at ZnS:N/(n^+,p^+)–GaAs interfaces, 124
ZnS/GaP
In situ monitoring of ZnS/GaP and ZnSe/GaAs metalorganic vapor phase epitaxy using reflectance anisotropy spectroscopy and spectroscopic ellipsometry, 12
ZnSe
Raman and electroreflectance analysis of internal electric fields in ZnSe, 119
ZnSe/GaAs
In situ monitoring of ZnS/GaP and ZnSe/GaAs metalorganic vapor phase epitaxy using reflectance anisotropy spectroscopy and spectroscopic ellipsometry, 12